

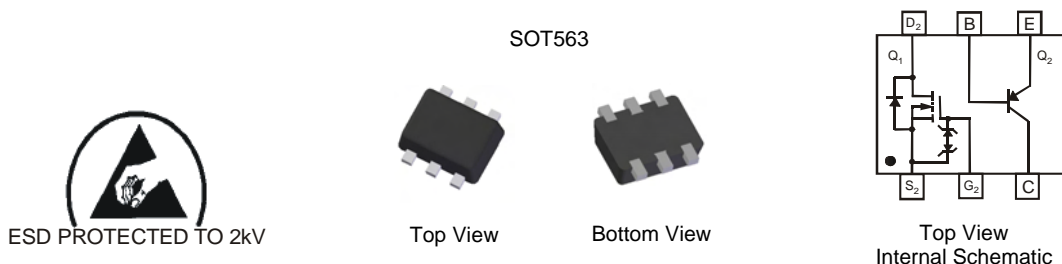
# N-CHANNEL ENHANCEMENT MODE MOSFET PLUS PNP TRANSISTOR

## Features

- N-Channel MOSFET and PNP Transistor in One Package
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V max
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **ESD Protected MOSFET Gate up to 2kV**
- **Lead, Halogen and Antimony Free, RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish - Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (approximate)

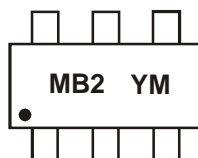


## Ordering Information (Note 3)

Part Number	Case	Packaging
DMB54D0UV-7	SOT563	3,000/Tape & Reel
DMB54D0UV-13	SOT563	10,000/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. No purposely added lead. Halogen and Antimony free
  2. Diodes Inc.'s "Green" policy can be found on our website at <http://www.diodes.com>.
  3. For packaging details, go to our website at <http://www.diodes.com>.

## Marking Information



MB2 = Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: V = 2008)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	V	W	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings – MOSFET, Q1** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V <sub>DSS</sub>	50	V
Gate-Source Voltage	V <sub>GSS</sub>	±12	V
Drain Current (Note 4) Continuous	I <sub>D</sub>	160	mA
Pulsed Drain Current (Note 4)	I <sub>DM</sub>	560	mA

**Maximum Ratings - PNP Transistor, Q2** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-45	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	V
Collector Current	I <sub>C</sub>	-100	mA

**Thermal Characteristics, Total Device** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 4)	P <sub>D</sub>	250	mW
Thermal Resistance, Junction to Ambient (Note 4)	R <sub>θJA</sub>	500	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics - MOSFET** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 5)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	50	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	10	μA	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V
Gate-Body Leakage	I <sub>GSS</sub>	—	—	1.0 5.0	μA	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 5)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.7	0.8	1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	3.1	4	Ω	V <sub>GS</sub> = 4V, I <sub>D</sub> = 100mA
		—	4	5		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 80mA
Forward Transconductance	g <sub>FS</sub>	180	—	—	mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 100mA, f = 1.0KHz
<b>DYNAMIC CHARACTERISTICS (Note 6)</b>						
Input Capacitance	C <sub>iss</sub>	—	25	—	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	5	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	2.1	—	pF	

- Notes: 4. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.  
5. Short duration pulse test used to minimize self-heating effect.  
6. Guaranteed by design. Not subject to product testing.

## Electrical Characteristics - PNP Transistor @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage (Note 5)	V <sub>(BR)CBO</sub>	-50	—	—	V	I <sub>C</sub> = 10μA, I <sub>B</sub> = 0
Collector-Emitter Breakdown Voltage (Note 5)	V <sub>(BR)CEO</sub>	-45	—	—	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage (Note 5)	V <sub>(BR)EBO</sub>	-5	—	—	V	I <sub>E</sub> = 1μA, I <sub>C</sub> = 0
DC Current Gain (Note 5)	h <sub>FE</sub>	220	290	475	—	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -2.0mA
Collector-Emitter Saturation Voltage (Note 5)	V <sub>CE(SAT)</sub>	—	—	-100 -400	mV	I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA I <sub>C</sub> = -100mA, I <sub>B</sub> = -5.0mA
Base-Emitter Saturation Voltage (Note 5)	V <sub>BE(SAT)</sub>	—	-700 -900	—	mV	I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA I <sub>C</sub> = -100mA, I <sub>B</sub> = -5.0mA
Base-Emitter Voltage (Note 5)	V <sub>BE(ON)</sub>	-600 —	—	-750 -820	mV	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -2.0mA V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -10mA
Collector-Cutoff Current (Note 5)	I <sub>CBO</sub>	—	—	-15 -4.0	nA μA	V <sub>CB</sub> = -30V V <sub>CB</sub> = -30V, T <sub>A</sub> = 150°C
Collector-Emitter Cut-Off Current (Note 5)	I <sub>CES</sub>	—	—	-100	nA	V <sub>CE</sub> = -45V
Gain Bandwidth Product	f <sub>T</sub>	100	—	—	MHz	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -10mA, f = 100MHz
Output Capacitance	C <sub>OB</sub>	—	—	4.5	pF	V <sub>CB</sub> = -10V, f = 1.0MHz
Noise Figure	NF	—	—	10	dB	I <sub>C</sub> = -0.2mA, V <sub>CE</sub> = -5.0Vdc, R <sub>S</sub> = 2.0KΩ, f = 1.0KHz, BW = 200Hz

## MOSFET

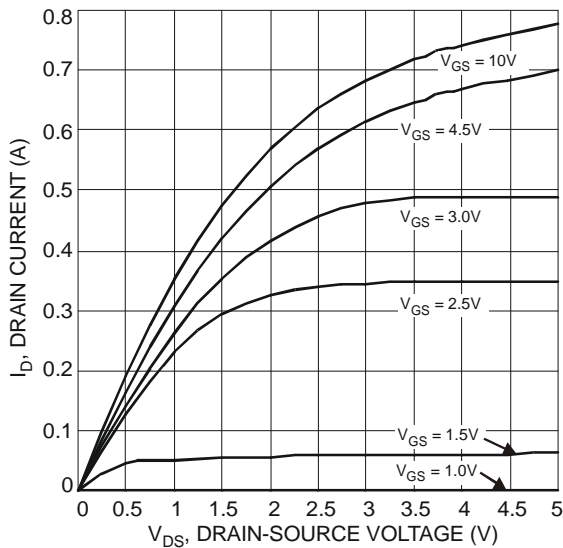


Fig. 1 Typical Output Characteristics

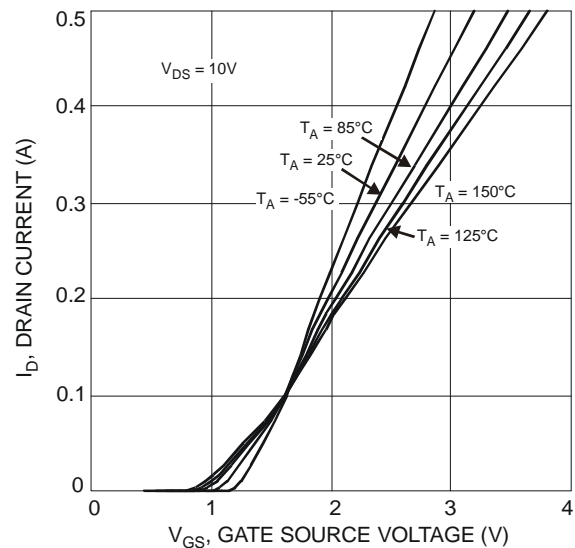


Fig. 2 Typical Transfer Characteristics

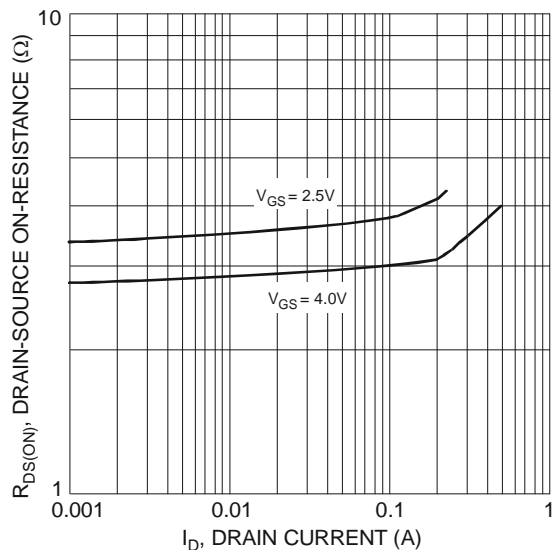


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

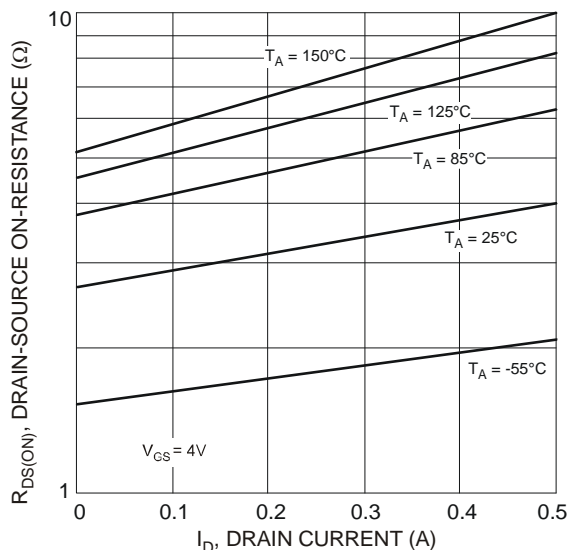


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

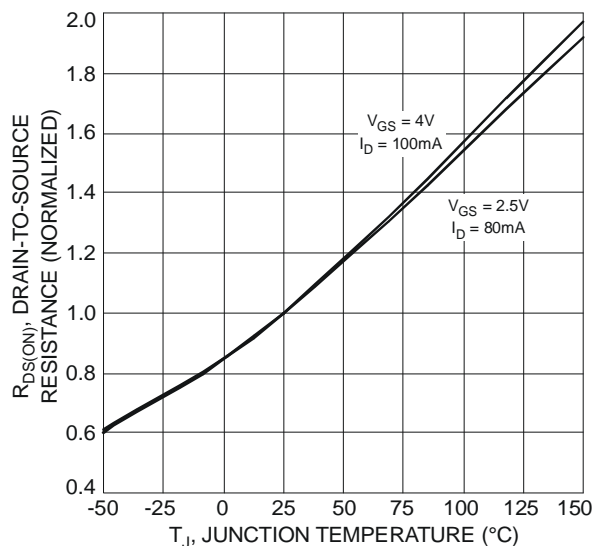


Fig. 5 On-Resistance Variation with Temperature

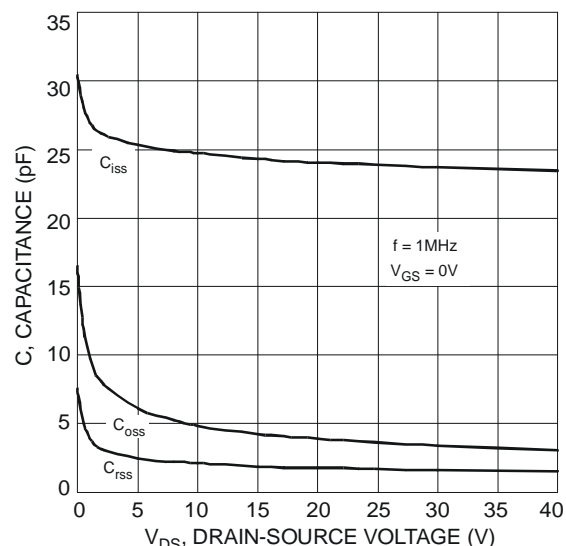


Fig. 6 Typical Capacitance

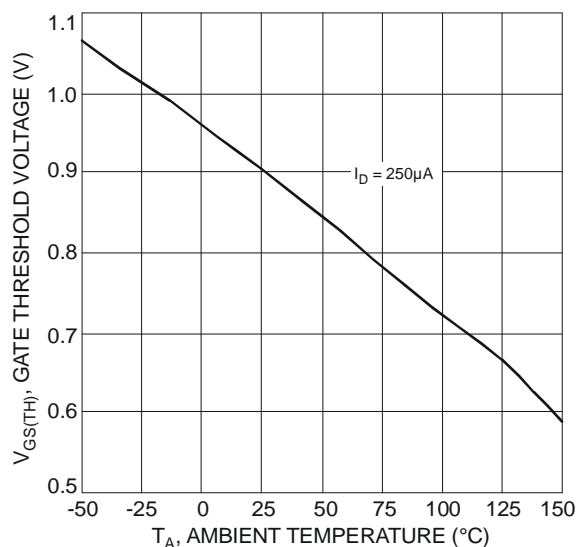


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

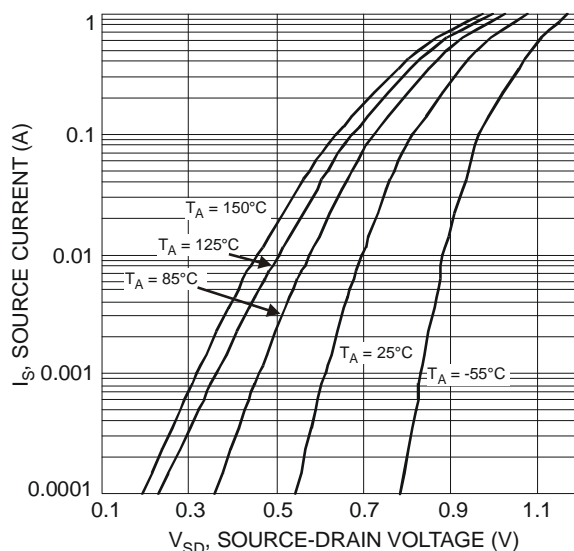


Fig. 8 Diode Forward Voltage vs. Current

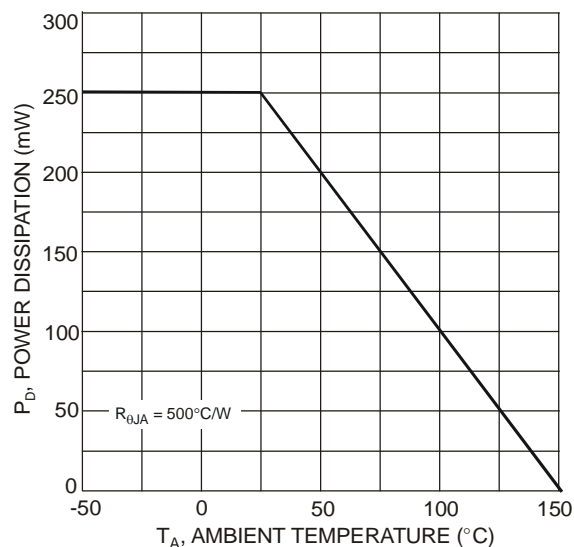


Fig. 9 Derating Curve - Total Package Power Dissipation

## PNP Transistor

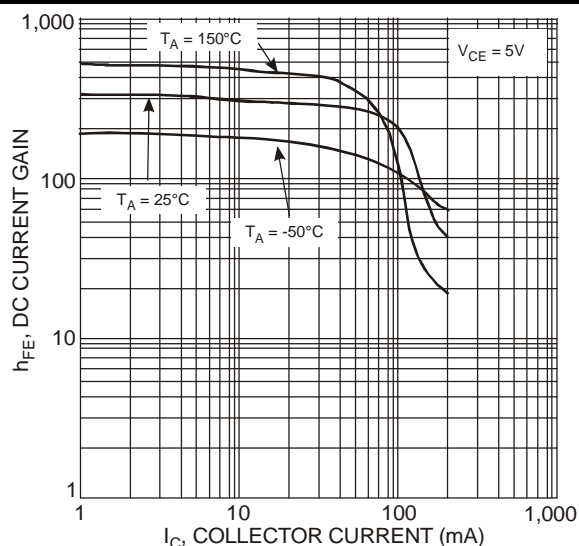


Fig. 10 Typical DC Current Gain vs. Collector Current

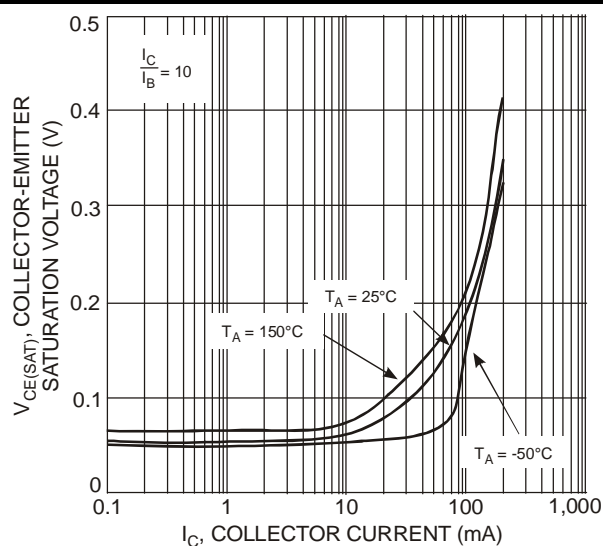


Fig. 11 Collector-Emitter Saturation Voltage vs. Collector Current

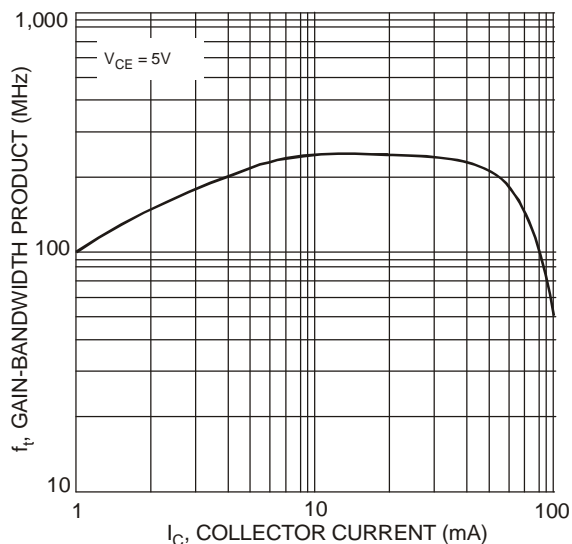
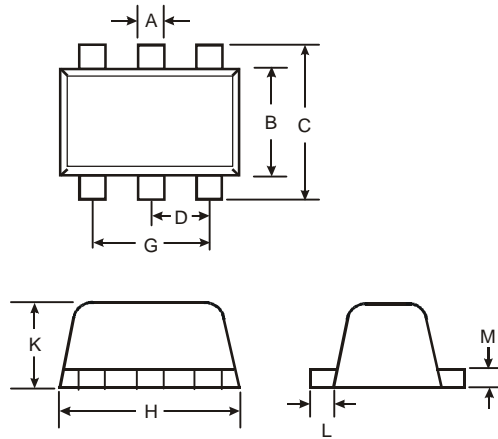


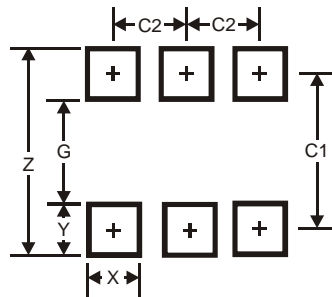
Fig. 12 Typical Gain-Bandwidth Product vs. Collector Current

## Package Outline Dimensions



SOT563			
Dim	Min	Max	Typ
A	0.15	0.30	0.20
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	-	-	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.55	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

## Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Y	0.5
C1	1.7
C2	0.5

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